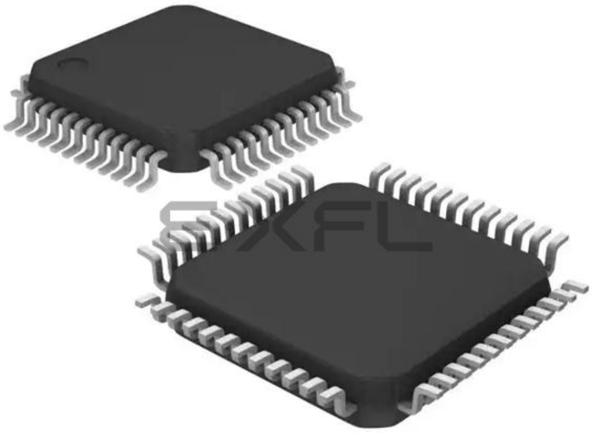
NXP USA Inc. - MCF51QU64VLF Datasheet



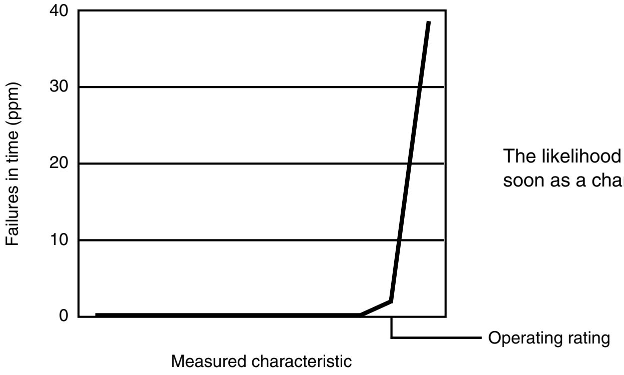
Details	
Product Status	Active
Core Processor	Coldfire V1
Core Size	32-Bit Single-Core
Speed	50MHz
Connectivity	EBI/EMI, I²C, SPI, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	35
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 13x12b; D/A 1x12b
Oscillator Type	External
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mcf51qu64vlf

3.4.1 Example

This is an example of an operating rating:

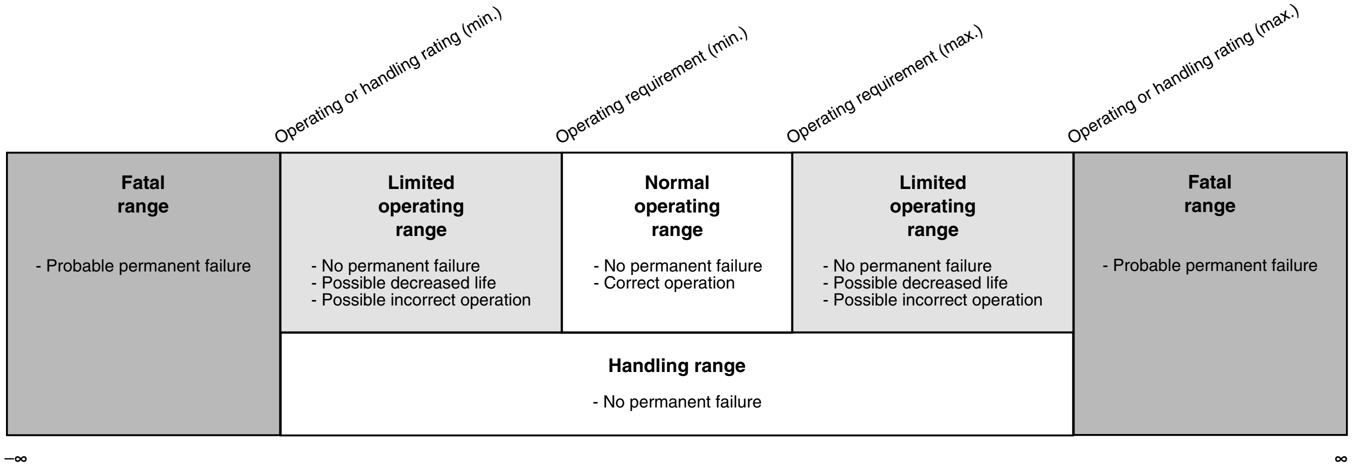
Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	–0.3	1.2	V

3.5 Result of exceeding a rating



The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.

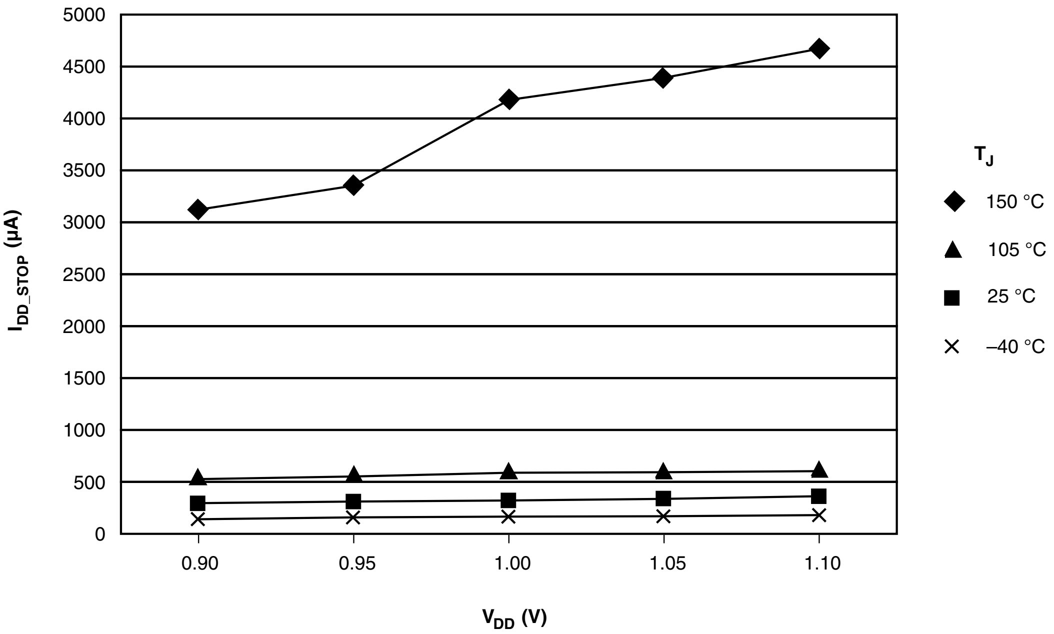
3.6 Relationship between ratings and operating requirements



3.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.



4 Ratings

4.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T_{STG}	Storage temperature	–55	150	°C	1
T_{SDR}	Solder temperature, lead-free	—	260	°C	2
	Solder temperature, leaded	—	245		

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

5.2.3 Voltage and current operating behaviors

Table 3. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{OH}	Output high voltage — high drive strength				
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = - 9 mA	V_{DD} – 0.5	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -3 mA	V_{DD} – 0.5	—	V	
	Output high voltage — low drive strength				
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = -2 mA	V_{DD} – 0.5	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = -0.6 mA	V_{DD} – 0.5	—	V	
I_{OHT}	Output high current total for all ports	—	100	mA	
V_{OL}	Output low voltage — high drive strength				
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 9 mA	—	0.5	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 3 mA	—	0.5	V	
	Output low voltage — low drive strength				
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 2 mA	—	0.5	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 0.6 mA	—	0.5	V	
I_{OLT}	Output low current total for all ports	—	100	mA	
I_{IN}	Input leakage current (per pin)				1
	• @ full temperature range	—	1.0	μA	
	• @ 25 °C	—	0.1	μA	
I_{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	μA	
I_{OZ}	Total Hi-Z (off-state) leakage current (all input pins)	—	4	μA	
R_{PU}	Internal pullup resistors	22	50	kΩ	2
R_{PD}	Internal pulldown resistors	22	50	kΩ	3

1. Tested by ganged leakage method
2. Measured at Vinput = V_{SS}
3. Measured at Vinput = V_{DD}

5.2.4 Power mode transition operating behaviors

All specifications except t_{POR} and VLLSx-RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 50 MHz
- Bus clock (and flash and Mini-FlexBus clocks) = 25 MHz

Table 5. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DD_RUN}	Run mode current — all peripheral clocks enabled, code executing from RAM, exercising flash memory • @ 1.8 V • @ 3.0 V	— —	20 20	23.5 25	mA mA	3
I_{DD_WAIT}	Wait mode current at 3.0 V — all peripheral clocks disabled	—	5.8	6.8	mA	4
I_{DD_STOP}	Stop mode current at 3.0 V • @ –40 to 25 °C • @ 105 °C	— —	0.34 0.90	0.41 1.8	mA mA	
I_{DD_VLPR}	Very low-power run mode current at 3.0 V — all peripheral clocks disabled	—	0.63	1.32	mA	5
I_{DD_VLPR}	Very low-power run mode current at 3.0 V — all peripheral clocks enabled	—	0.78	1.46	mA	6
I_{DD_VLPW}	Very low-power wait mode current at 3.0 V	—	0.15	0.62	mA	7
I_{DD_VLPS}	Very low-power stop mode current at 3.0 V • @ –40 to 25 °C • @ 105 °C	— —	19 145	45 312	µA	8
I_{DD_LLS}	Low leakage stop mode current at 3.0 V • @ –40 to 25 °C • @ 105 °C	— —	3.0 53.3	4.8 157	µA µA	8,9,10
I_{DD_VLLS3}	Very low-leakage stop mode 3 current at 3.0 V • @ –40 to 25 °C • @ 105 °C	— —	1.8 39.2	3.3 115	µA µA	8,9,10
I_{DD_VLLS2}	Very low-leakage stop mode 2 current at 3.0 V • @ –40 to 25 °C • @ 105 °C	— —	1.6 22.2	2.8 65	µA µA	8,9
I_{DD_VLLS1}	Very low-leakage stop mode 1 current at 3.0 V • @ –40 to 25 °C • @ 105 °C	— —	1.4 17.6	2.6 50	µA µA	8,9
I_{DD_RTC}	Average current adder for real-time clock function • @ –40 to 25 °C	—	0.7	—	µA	11

1. The analog supply current is the sum of the active current for each of the analog modules on the device. See each module's specification for its supply current.
2. 50 MHz core and system clocks, and 25 MHz bus clock. MCG configured for FEI mode. All peripheral clocks disabled.
3. 50 MHz core and system clocks, and 25 MHz bus clock. MCG configured for FEI mode. All peripheral clocks enabled, but peripherals are not in active operation.
4. 50 MHz core and system clocks, and 25 MHz bus clock. MCG configured for FEI mode.

The following general purpose specifications apply to all signals configured for RGPIO, FTM, and UART. The conditions are 25 pf load, V_{DD} = 3.6 V to 1.71 V, and full temperature range. The GPIO are set for high drive, no slew rate control, and no input filter, digital or analog, unless otherwise specified.

Table 10. RGPIO General Control Timing

Symbol	Description	Min.	Max.	Unit
R1	CPUCLK from CLK_OUT pin high to GPIO output valid	—	16	ns
R2	CPUCLK from CLK_OUT pin high to GPIO output invalid (output hold)	1	—	ns
R3	GPIO input valid to bus clock high	17	—	ns
R4	CPUCLK from CLK_OUT pin high to GPIO input invalid	—	2	ns

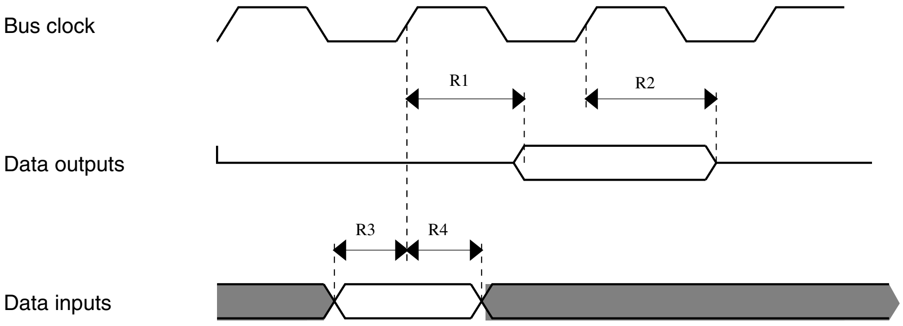


Figure 4. RGPIO timing diagram

5.4 Thermal specifications

5.4.1 Thermal operating requirements

Table 11. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_J	Die junction temperature	–40	115	°C
T_A	Ambient temperature	–40	105	°C

6.3.2.2 Oscillator frequency specifications

Table 16. Oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal or resonator frequency — low frequency mode (MCG_C2[RANGE]=00)	32	—	40	kHz	
$f_{osc\_hi\_1}$	Oscillator crystal or resonator frequency — high frequency mode (low range) (MCG_C2[RANGE]=01)	1	—	8	MHz	
$f_{osc\_hi\_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	—	32	MHz	
f_{ec_extal}	Input clock frequency (external clock mode)	—	—	50	MHz	1, 2
t_{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t_{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	—	750	—	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—	250	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	—	0.6	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	—	1	—	ms	

1. Other frequency limits may apply when external clock is being used as a reference for the FLL or PLL.
2. When transitioning from FBE to FEI mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.
3. Proper PC board layout procedures must be followed to achieve specifications.
4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

6.4 Memories and memory interfaces

6.4.1 Flash (FTFL) electrical specifications

This section describes the electrical characteristics of the FTFL module.

6.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 17. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{hvpgm4}	Longword Program high-voltage time	—	7.5	18	μs	
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{hversblk32k}$	Erase Block high-voltage time for 32 KB	—	52	452	ms	1
$t_{hversblk128k}$	Erase Block high-voltage time for 128 KB	—	208	1808	ms	1

1. Maximum time based on expectations at cycling end-of-life.

6.4.1.2 Flash timing specifications — commands

Table 18. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	Read 1s Block execution time					
$t_{rd1blk32k}$	• 32 KB data flash	—	—	0.5	ms	
$t_{rd1blk128k}$	• 128 KB program flash	—	—	1.7	ms	
$t_{rd1sec1k}$	Read 1s Section execution time (data flash sector)	—	—	60	μs	1
t_{pgmchk}	Program Check execution time	—	—	45	μs	1
t_{rdrsrc}	Read Resource execution time	—	—	30	μs	1
t_{pgm4}	Program Longword execution time	—	65	145	μs	
	Erase Flash Block execution time					2
$t_{ersblk32k}$	• 32 KB data flash	—	55	465	ms	
$t_{ersblk128k}$	• 128 KB program flash	—	220	1850	ms	
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
	Program Section execution time					
$t_{pgmsec512}$	• 512 B flash	—	4.7	—	ms	
$t_{pgmsec1k}$	• 1 KB flash	—	9.3	—	ms	
t_{rd1all}	Read 1s All Blocks execution time	—	—	1.8	ms	
t_{rdonce}	Read Once execution time	—	—	25	μs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	μs	
t_{ersall}	Erase All Blocks execution time	—	275	2350	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	μs	1
	Program Partition for EEPROM execution time					
$t_{pgmpart32k}$	• 32 KB FlexNVM	—	70	—	ms	

Table continues on the next page...

Table 22. Flexbus switching specifications (continued)

Num	Description	Min.	Max.	Unit	Notes
FB2	Address, data, and control output valid	—	20	ns	1
FB3	Address, data, and control output hold	1	—	ns	1
FB4	Data and $\overline{\text{FB\_TA}}$ input setup	20	—	ns	2
FB5	Data and $\overline{\text{FB\_TA}}$ input hold	10	—	ns	2

1. Specification is valid for all FB_AD[31:0], $\overline{\text{FB\_CS}n}$, $\overline{\text{FB\_OE}}$, FB_R/$\overline{\text{W}}$, and $\overline{\text{FB\_TS}}$.
2. Specification is valid for all FB_AD[31:0].

Note

The following diagrams refer to signal names that may not be included on your particular device. Ignore these extraneous signals.

Also, ignore the AA=0 portions of the diagrams because this setting is not supported in the Mini-FlexBus.

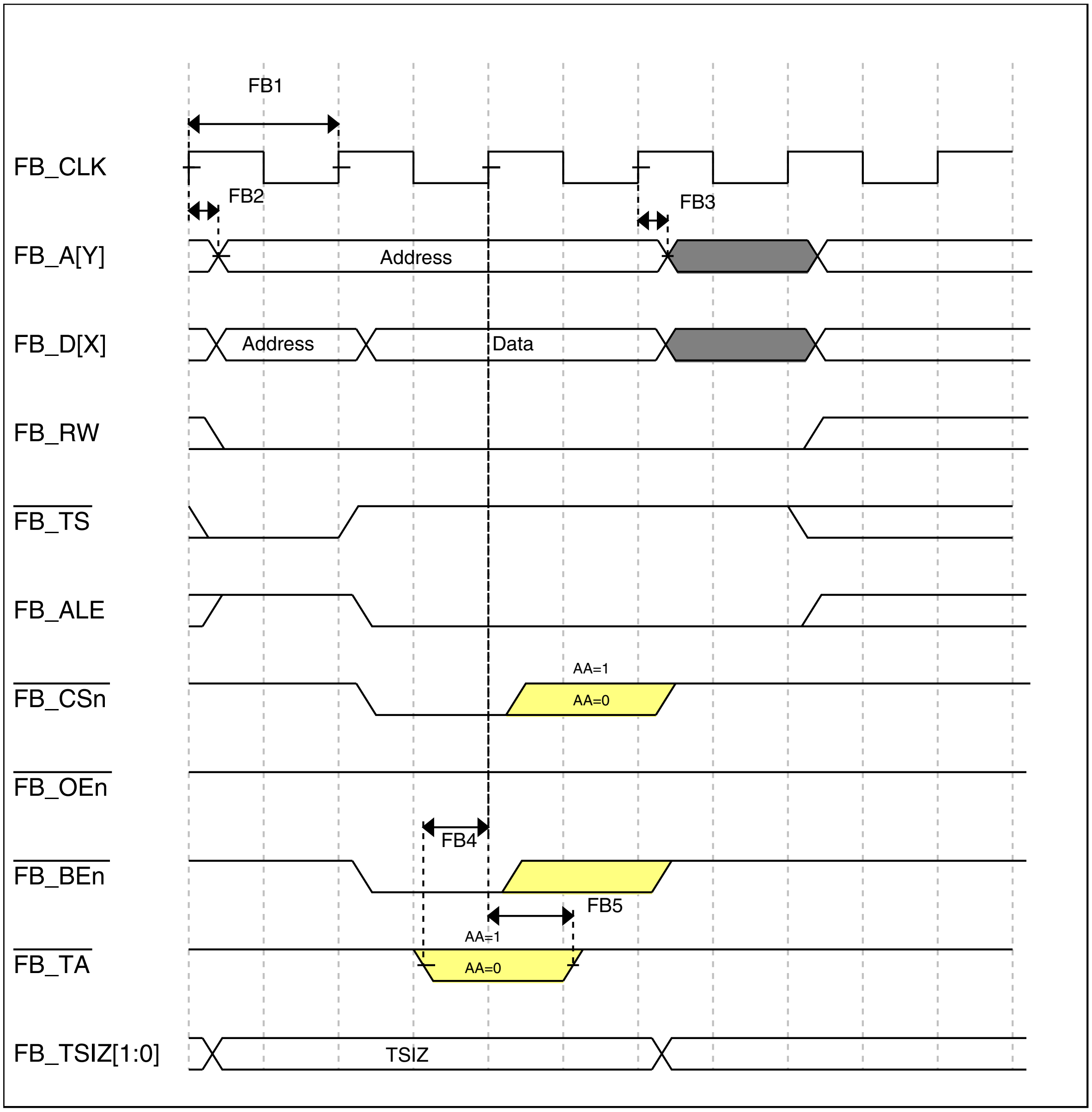


Figure 8. Mini-FlexBus write timing diagram

6.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

5. For guidelines and examples of conversion rate calculation, download the ADC calculator tool: http://cache.freescale.com/files/soft_dev_tools/software/app_software/converters/ADC_CALCULATOR_CNV.zip?fpsp=1

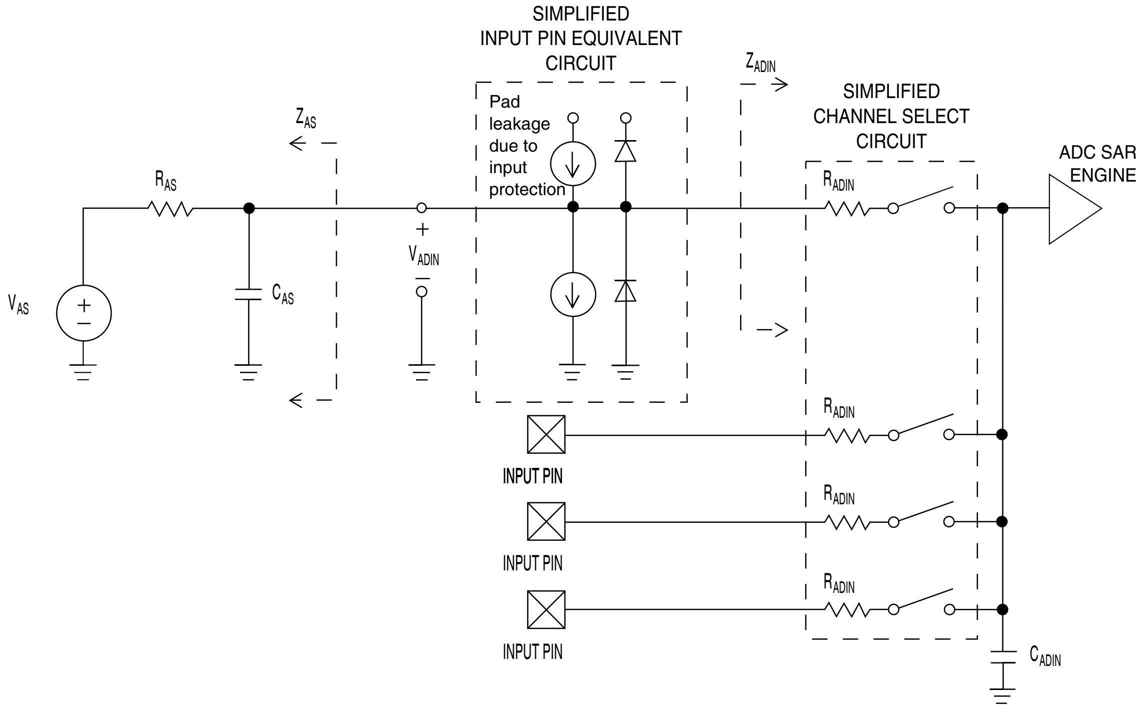


Figure 9. ADC input impedance equivalency diagram

6.6.1.2 12-bit ADC electrical characteristics

Table 24. 12-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
I_{DDA_ADC}	Supply current		0.215	—	1.7	mA	3
f_{ADACK}	ADC asynchronous clock source	• ADLPC=1, ADHSC=0 • ADLPC=1, ADHSC=1 • ADLPC=0, ADHSC=0 • ADLPC=0, ADHSC=1	1.2 3.0 2.4 4.4	2.4 4.0 5.2 6.2	3.9 7.3 6.1 9.5	MHz MHz MHz MHz	$t_{ADACK} = 1/f_{ADACK}$
	Sample Time	See Reference Manual chapter for sample times					
TUE	Total unadjusted error	• 12 bit modes • <12 bit modes	— —	±4 ±1.4	±6.8 ±2.1	LSB[4]	5
DNL	Differential non-linearity	• 12 bit modes • <12 bit modes	— —	±0.7 ±0.2	-1.1 to +1.9 -0.3 to 0.5	LSB[4]	5
INL	Integral non-linearity	• 12 bit modes • <12 bit modes	— —	±1.0 ±0.5	-2.7 to +1.9 -0.7 to +0.5	LSB[4]	5

Table continues on the next page...

Table 25. Comparator and 6-bit DAC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
V_H	Analog comparator hysteresis[1]				
	• CR0[HYSTCTR] = 00	—	5	—	mV
	• CR0[HYSTCTR] = 01	—	10	—	mV
	• CR0[HYSTCTR] = 10	—	20	—	mV
	• CR0[HYSTCTR] = 11	—	30	—	mV
V_{CMPOh}	Output high	V_{DD} – 0.5	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN=1, PMODE=1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN=1, PMODE=0)	80	250	600	ns
	Analog comparator initialization delay[2]	—	—	40	μs
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	μA
INL	6-bit DAC integral non-linearity	–0.5	—	0.5	LSB[3]
DNL	6-bit DAC differential non-linearity	–0.3	—	0.3	LSB

[1] Typical hysteresis is measured with input voltage range limited to 0.6 to V_{DD}-0.6V.

[2] Comparator initialization delay is defined as the time between software writes to change control inputs (Writes to DACEN, VRSEL, PSEL, MSEL, VOSEL) and the comparator output settling to a stable level.

[3] 1 LSB = $V_{reference}$/64

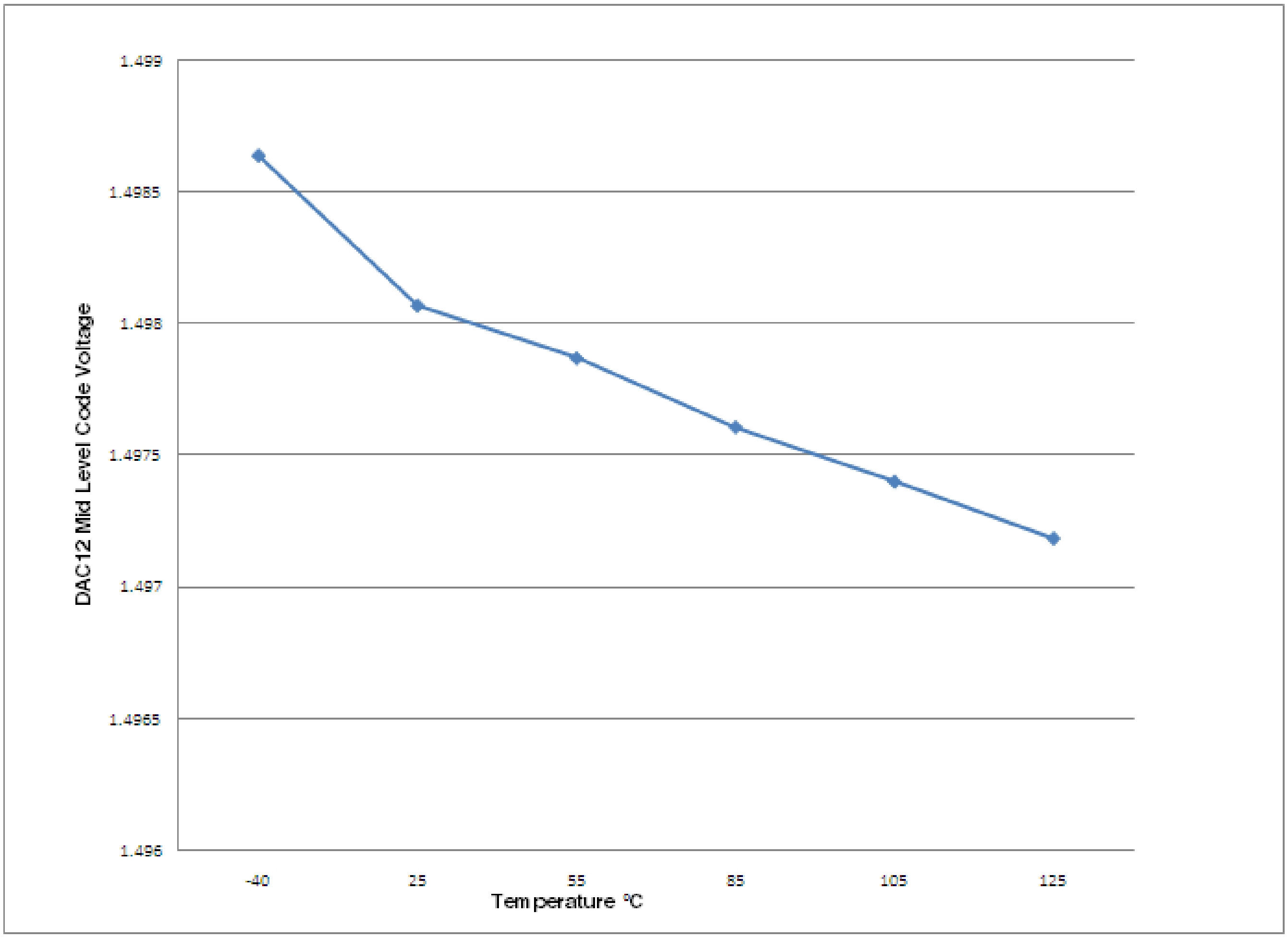


Figure 13. Offset at half scale vs. temperature

6.6.4 Voltage reference electrical specifications

Table 28. VREF full-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage	1.71	3.6	V	
T_A	Temperature	–40	105	°C	
C_L	Output load capacitance	100		nF	1

1. C_L must be connected to VREF_OUT if the VREF_OUT functionality is being used for either an internal or external reference.

Table 29. VREF full-range operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim at nominal V_{DDA} and temperature=25C	1.1965	1.2	1.2027	V	
V_{out}	Voltage reference output with— factory trim	1.1584	—	1.2376	V	
V_{out}	Voltage reference output — user trim	1.198	—	1.202	V	
V_{step}	Voltage reference trim step	—	0.5	—	mV	
V_{tdrift}	Temperature drift (Vmax -Vmin across the full temperature range)	—	—	80	mV	
I_{bg}	Bandgap only (MODE_LV = 00) current	—	—	80	μA	
I_{tr}	Tight-regulation buffer (MODE_LV =10) current	—	—	1.1	mA	
ΔV_{LOAD}	Load regulation (MODE_LV = 10) • current = + 1.0 mA • current = - 1.0 mA	 — —	 2 5	 — —	mV	1
T_{stup}	Buffer startup time	—	—	100	μs	
V_{vdrift}	Voltage drift (Vmax -Vmin across the full voltage range) (MODE_LV = 10, REGEN = 1)	—	2	—	mV	

1. Load regulation voltage is the difference between the VREF_OUT voltage with no load vs. voltage with defined load

Table 30. VREF limited-range operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_A	Temperature	0	50	°C	

Table 31. VREF limited-range operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{out}	Voltage reference output with factory trim	1.173	1.225	V	

6.7 Timers

See General Switching Specifications.

Table 33. SPI slave mode timing (continued)

Num.	Symbol	Description	Min.	Max.	Unit	Comment
2	t_{SPSCK}	SPSCK period	4 x t_{BUS}	—	ns	t_{BUS} = 1/ f_{BUS}
3	t_{Lead}	Enable lead time	1	—	t_{BUS}	—
4	t_{Lag}	Enable lag time	1	—	t_{BUS}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{BUS} - 30	—	ns	—
6	t_{SU}	Data setup time (inputs)	19.5	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—
8	t_a	Slave access time	—	t_{BUS}	ns	Time to data active from high-impedance state
9	t_{dis}	Slave MISO disable time	—	t_{BUS}	ns	Hold time to high-impedance state
10	t_v	Data valid (after SPSCK edge)	—	27	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	t_{BUS} - 25	ns	—
	t_{FI}	Fall time input				
13	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output				

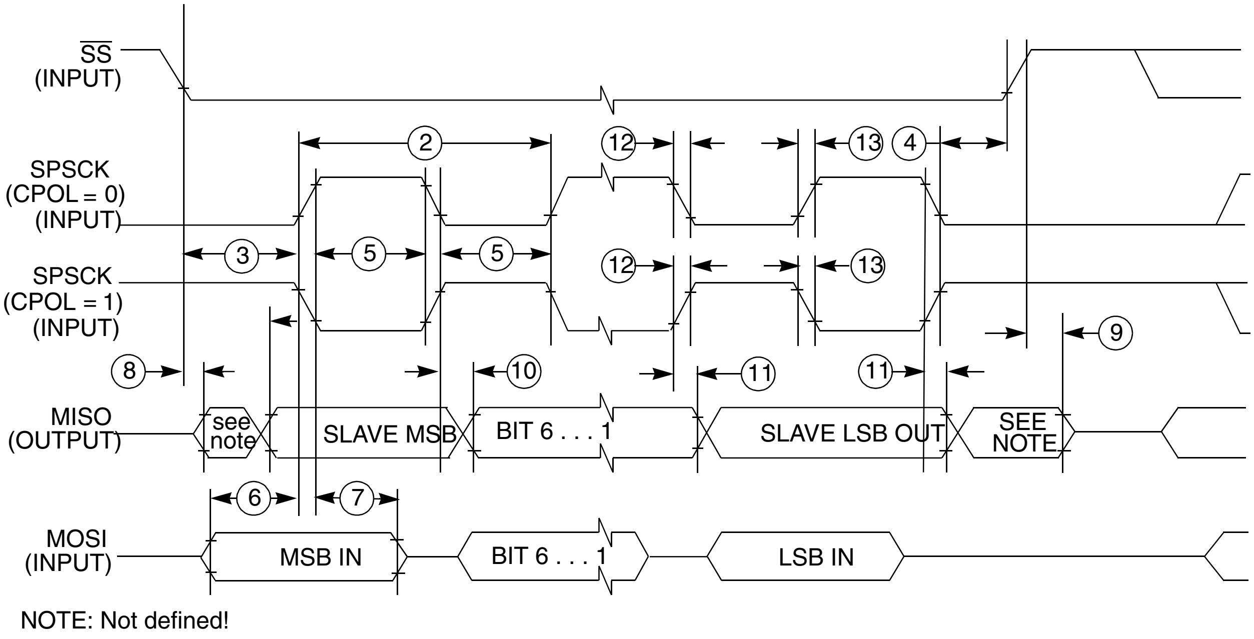


Figure 16. SPI slave mode timing (CPHA=0)

8 Pinout

8.1 Signal Multiplexing and Pin Assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Mux Control module is responsible for selecting which ALT functionality is available on each pin.

NOTE

- On PTB0, EZP_MS_b is active only during reset. Refer to the detailed boot description.
- PTC1 is open drain.

64-pin	48-pin	44-pin	32-pin	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
1	—	—	—	VDD	VDD								
2	—	—	—	VSS	VSS								
3	—	—	—	Disabled	Disabled	PTC6	UART0_TX	I2C0_SCL	RGPIO6	SPI1_MOSI	FBa_AD11		
4	—	—	—	Disabled	Disabled	PTC7	UART0_RX	I2C0_SDA	RGPIO7	SPI1_MISO	FBa_AD12		
5	1	—	—	Disabled	Disabled	PTD0	UART0_CTS_b	I2C1_SDA	RGPIO8	SPI1_SCLK	FBa_AD13		
6	2	—	—	Disabled	Disabled	PTD1	UART0_RTS_b	I2C1_SCL	RGPIO9	SPI1_SS	FBa_AD14		
7	3	1	1	Disabled	Disabled	PTA0		I2C2_SCL	FTM1_CH0	SPI0_SS	FBa_AD15		
8	4	2	2	Disabled	Disabled	PTA1		I2C2_SDA	FTM1_CH1		FBa_AD16		
9	5	3	3	Disabled	Disabled	PTA2	UART1_TX		FTM1_CH2	SPI1_SS			
10	6	4	4	Disabled	Disabled	PTA3	UART1_RX		FTM1_CH3	SPI1_SCLK			EZP_CLK
11	7	5	5	ADC0_SE2	ADC0_SE2	PTA4	UART1_CTS_b	I2C2_SCL	FTM1_CH4	SPI1_MISO			EZP_DI
12	8	6	6	ADC0_SE3	ADC0_SE3	PTA5	UART1_RTS_b	I2C2_SDA	FTM1_CH5	SPI1_MOSI	CLKOUT		EZP_DO
13	9	7	7	VDDA	VDDA								
14	10	8	—	VREFH	VREFH								
15	11	9	—	VREF_OUT	VREF_OUT								
16	12	10	—	VREFL	VREFL								
17	13	11	8	VSSA	VSSA								
18	14	12	9	DAC0_OUT	DAC0_OUT								
19	15	13	10	ADC0_SE0	ADC0_SE0								
20	16	14	11	ADC0_SE1	ADC0_SE1								
21	17	15	12	VREGIN	VREGIN								
22	18	16	13	VOUT33	VOUT33								
23	19	17	14	VSS	VSS								

64-pin	48-pin	44-pin	32-pin	Default	ALT0	ALT1	ALT2	ALT3	ALT4	ALT5	ALT6	ALT7	EzPort
49	36	32	25	VSS	VSS								
50	37	33	26	EXTAL1	EXTAL1	PTB7		I2C1_SDA	TMR_CLKIN1				
51	38	34	27	XTAL1	XTAL1	PTC0		I2C1_SCL	TMR_CLKIN0	RGPIO0			
52	39	35	28	RESET_b	Disabled	PTC1	RESET_b						
53	—	—	—	CMP0_IN0	CMP0_IN0	PTF0	SPI0_SS				FBa_AD5		
54	—	—	—	Disabled	Disabled	PTF1	SPI0_SCLK			CMP0_OUT	FBa_AD6		
55	—	—	—	CMP0_IN1	CMP0_IN1	PTF2	SPI0_MISO				FBa_AD7		
56	40	36	—	CMP0_IN2	CMP0_IN2	PTF3	SPI0_MOSI			RGPIO1	FBa_AD8		
57	41	37	29	CMP0_IN3	CMP0_IN3	PTC2	UART1_RTS_b	SPI1_SS		RGPIO2	FBa_AD18		
58	42	38	—	Disabled	Disabled	PTF4	UART1_CTS_b	SPI1_SCLK		FBa_D3	FBa_AD19		
59	43	39	—	Disabled	Disabled	PTF5	UART1_RX	SPI1_MISO		FBa_D2	FBa_RW_b		
60	44	40	—	Disabled	Disabled	PTF6	UART1_TX	SPI1_MOSI		FBa_D1	FBa_AD9		
61	45	41	—	Disabled	Disabled	PTF7	UART0_RTS_b		SPI0_SS	FBa_D0	FBa_AD10		
62	46	42	30	Disabled	Disabled	PTC3	UART0_CTS_b	RGPIO3	SPI0_SCLK	CLKOUT			
63	47	43	31	Disabled	Disabled	PTC4	UART0_RX	RGPIO4	SPI0_MISO	PDB0_EXTRG			
64	48	44	32	Disabled	Disabled	PTC5	UART0_TX	RGPIO5	SPI0_MOSI	CMT_IRO			

8.2 Pinout diagrams

The following diagrams show pinouts for the 64-pin, 48-pin, 44-pin, and 32-pin packages. These diagrams are representations for ease of reference. See the package drawings for mechanical details.

For each pin, the diagrams show the default function or (when disabled is the default) the ALT1 signal for a GPIO function. However, many signals may be multiplexed onto a single pin.

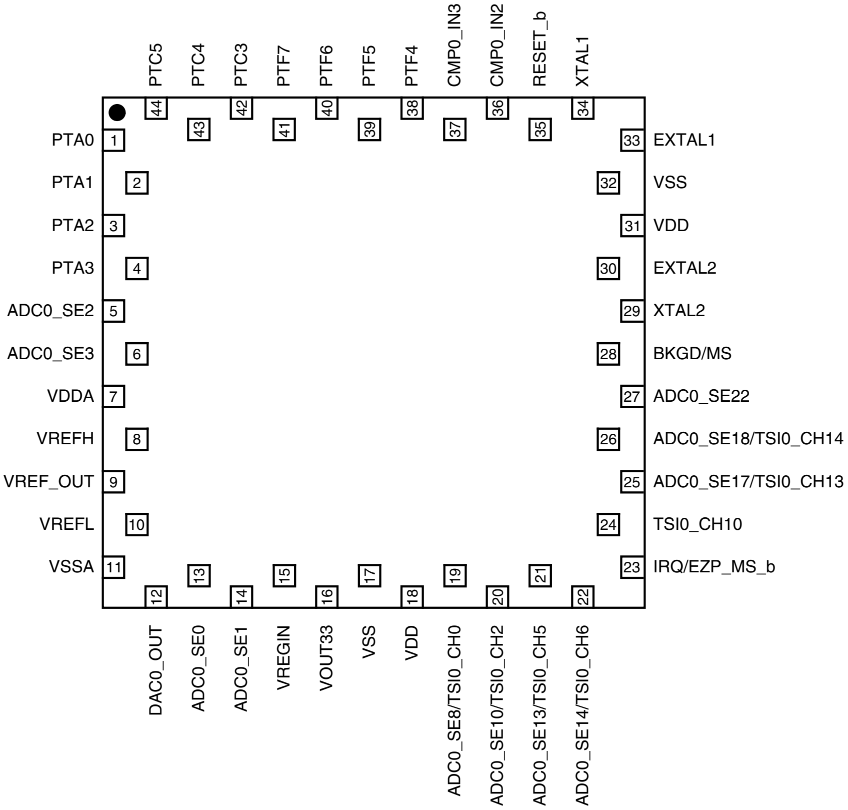


Figure 20. 44-pin Laminate QFN

Table 35. Module signals by GPIO port and pin (continued)

64-pin	48-pin	44-pin	32-pin	Port	Module signal(s)
48	35	31	24		VDD
2					VSS
23	19	17	14		VSS
49	36	32	25		VSS
System					
45	32	28	21	PTB4	BKGD/MS
12	8	6	6	PTA5	CLKOUT
62	46	42	30	PTC3	CLKOUT
10	6	4	4	PTA3	EZP_CLK
11	7	5	5	PTA4	EZP_DI
12	8	6	6	PTA5	EZP_DO
35	25	23	17	PTB0	IRQ/EZP_MS_b, EZP_CS_b
52	39	35	28	PTC1	RESET_b
OSC					
50	37	33	26	PTB7	EXTAL1
47	34	30	23	PTB6	EXTAL2
51	38	34	27	PTC0	XTAL1
46	33	29	22	PTB5	XTAL2
LLWU					
4				PTC7	LLWU_P0
6	2			PTD1	LLWU_P1
12	8	6	6	PTA5	LLWU_P2
30	23	21	16	PTA7	LLWU_P3
32				PTD7	LLWU_P4
35	25	23	17	PTB0	LLWU_P5
36	26	24	18	PTB1	LLWU_P6
39	27	25	19	PTB2	LLWU_P7
44	31	27		PTE7	LLWU_P8
45	32	28	21	PTB4	LLWU_P9
55				PTF2	LLWU_P10
56	40	36		PTF3	LLWU_P11
57	41	37	29	PTC2	LLWU_P12
59	43	39		PTF5	LLWU_P13
62	46	42	30	PTC3	LLWU_P14

Table continues on the next page...

Table 35. Module signals by GPIO port and pin (continued)

64-pin	48-pin	44-pin	32-pin	Port	Module signal(s)
44	31	27		PTE7	UART0_TX
64	48	44	32	PTC5	UART0_TX
UART1					
11	7	5	5	PTA4	UART1_CTS_b
58	42	38		PTF4	UART1_CTS_b
12	8	6	6	PTA5	UART1_RTS_b
57	41	37	29	PTC2	UART1_RTS_b
10	6	4	4	PTA3	UART1_RX
59	43	39		PTF5	UART1_RX
9	5	3	3	PTA2	UART1_TX
60	44	40		PTF6	UART1_TX

9 Revision History

The following table summarizes content changes since the previous release of this document.

Table 36. Revision History

Rev. No.	Date	Substantial Changes
4	01/2012	Thermal operating requirements: Changed maximum T_J value from 125°C to 115°C

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